

TENTATIVE TOSHIBA HYBRID DIGITAL INTEGRATED CIRCUIT 4,194,304-WORD BY 64-BIT SYNCHRONOUS DRAM MODULE DESCRIPTION

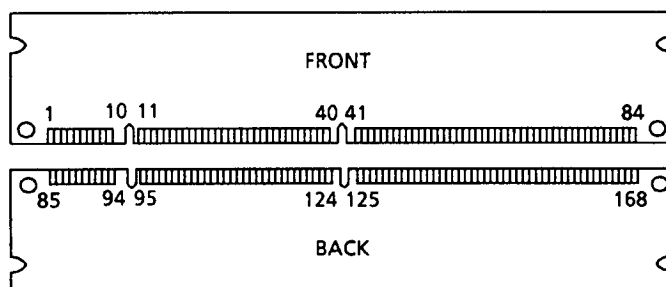
The THMY644071BEG is a 4,194,304-word by 64-bit synchronous dynamic RAM module consisting of four TC59S6416BFT/BFTL DRAMs and an unbuffer on a printed circuit board.

FEATURES

- 4,194,304-word by 64-bit organization
- Single power supply of 3.3 V $\pm$ 0.3 V
- Pipeline architecture
- Auto-refresh and Self-refresh capability
- All inputs and outputs LVTTTL-compatible
- 4096 refresh cycles per 64 ms
- Package: 168-pin DIMM Gold contacts
- Based on Intel Rev. 1.0 (4-clock)

	-80	-10
t _{CK} Clock Cycle Time (CL = 2)	8 ns	10 ns
t _{RAS} Active-to-Precharge Command Period (min)	48 ns	60 ns
t _{AC} Access Time from CLK (CL = 2)	6 ns	7 ns
t _{RC} Ref/Active-to-Ref/Active Command Period (min)	68 ns	84 ns

PIN ASSIGNMENT (TOP VIEW)



PIN NAMES

A0 to A11	Address Inputs
BA0, 1	Bank Select
DQ0 to DQ63	Data Inputs/Outputs
/CS0, 2	Chip Select
/RAS	Row Address Strobe
/CAS	Column Address Strobe
/WE	Write Enable
DQMB0 to 7	Output Disable/Write Mask
CLK0	Clock Input
CKE0	Clock Enable
SDA	Serial Data/Address for PD
SCL	Clock for PD
SA0 to 2	Address for PD
VDD	Power (+3.3 V)
VSS	Ground
NC	No Connection

1 VSS	85 VSS	29 DQMB1	113 DQMB5	57 DQ18	141 DQ50
2 DQ0	86 DQ32	30 /CS0	114 NC	58 DQ19	142 DQ51
3 DQ1	87 DQ33	31 NC	115 /RAS	59 VDD	143 VDD
4 DQ2	88 DQ34	32 VSS	116 VSS	60 DQ20	144 DQ52
5 DQ3	89 DQ35	33 A0	117 A1	61 NC	145 NC
6 VDD	90 VDD	34 A2	118 A3	62 NC	146 NC
7 DQ4	91 DQ36	35 A4	119 A5	63 NC	147 NC
8 DQ5	92 DQ37	36 A6	120 A7	64 VSS	148 VSS
9 DQ6	93 DQ38	37 A8	121 A9	65 DQ21	149 DQ53
10 DQ7	94 DQ39	38 A10	122 BA0	66 DQ22	150 DQ54
11 DQ8	95 DQ40	39 BA1	123 A11	67 DQ23	151 DQ55
12 VSS	96 VSS	40 VDD	124 VDD	68 VSS	152 VSS
13 DQ9	97 DQ41	41 VDD	125 CLK1	69 DQ24	153 DQ56
14 DQ10	98 DQ42	42 CLK0	126 NC	70 DQ25	154 DQ57
15 DQ11	99 DQ43	43 VSS	127 VSS	71 DQ26	155 DQ58
16 DQ12	100 DQ44	44 NC	128 CKE0	72 DQ27	156 DQ59
17 DQ13	101 DQ45	45 /CS2	129 NC	73 VDD	157 VDD
18 VDD	102 VDD	46 DQMB2	130 DQMB6	74 DQ28	158 DQ60
19 DQ14	103 DQ46	47 DQMB3	131 DQMB7	75 DQ29	159 DQ61
20 DQ15	104 DQ47	48 NC	132 NC	76 DQ30	160 DQ62
21 NC	105 NC	49 VDD	133 VDD	77 DQ31	161 DQ63
22 NC	106 NC	50 NC	134 NC	78 VSS	162 VSS
23 VSS	107 VSS	51 NC	135 NC	79 CLK2	163 CLK3
24 NC	108 NC	52 NC	136 NC	80 NC	164 NC
25 NC	109 NC	53 NC	137 NC	81 NC	165 SA0
26 VDD	110 VDD	54 VSS	138 VSS	82 SDA	166 SA1
27 /WE	111 /CAS	55 DQ16	139 DQ48	83 SCL	167 SA2
28 DQMB0	112 DQMB4	56 DQ17	140 DQ49	84 VDD	168 VDD

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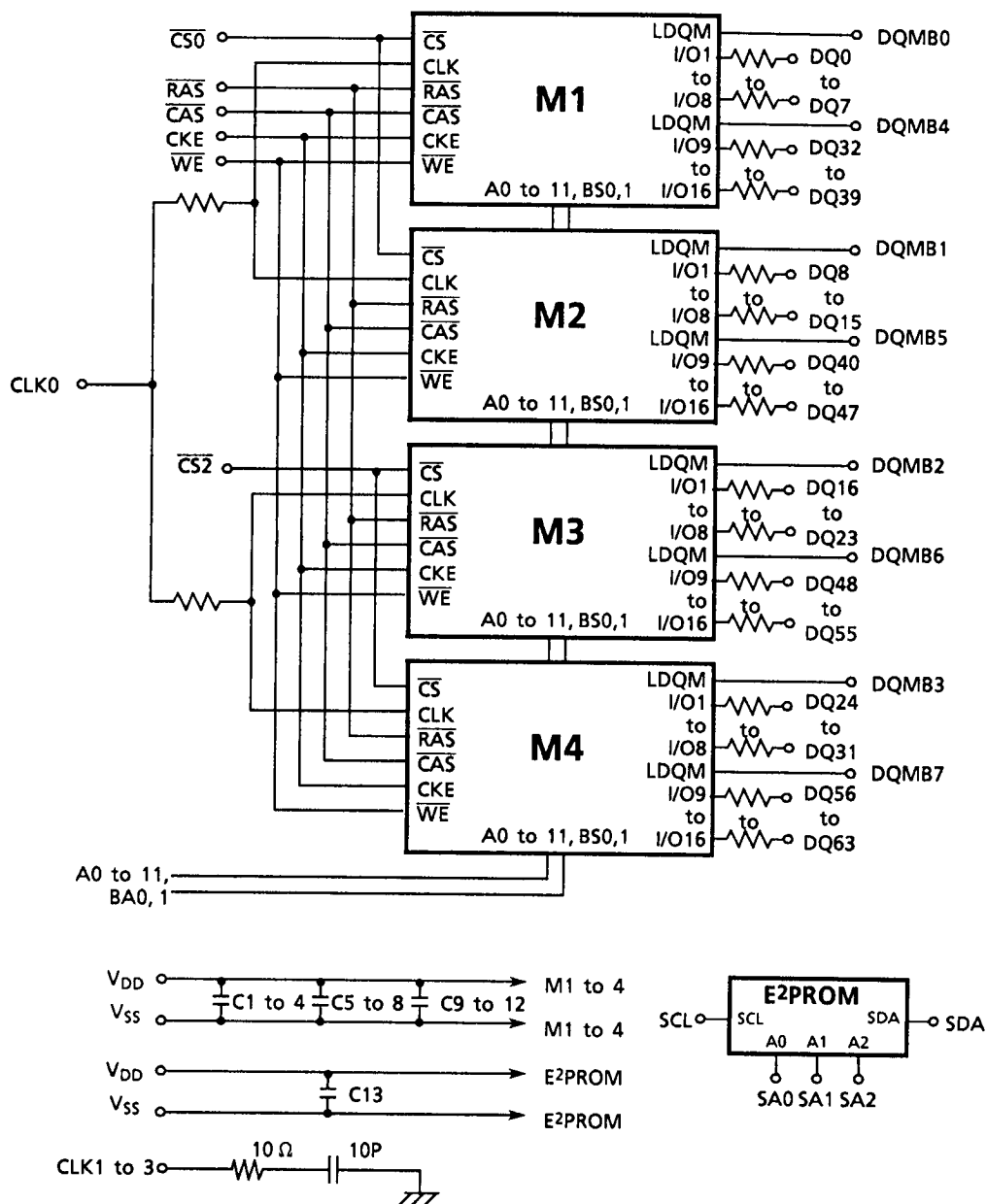
SERIAL PRESENCE DETECT (REV. 1.2A)

Byte Number	Function Described	-80		-10	
		Entry Value	Entry	Entry Value	Entry
0	Defines # Bytes Written into Serial Memory at Module mfg	128 Bytes	80h	128 Bytes	80h
1	Total # Bytes in SPD Memory Device	256 Bytes	08h	256 Bytes	08h
2	Fundamental Memory Type (FPM, EDO, SDRAM...) from Appendix A	SDRAM	04h	SDRAM	04h
3	# Row Addresses on this Assembly	RA0-RA11	0Ch	RA0-RA11	0Ch
4	# Column Addresses on this Assembly	CA0-CA7	08h	CA0-CA7	08h
5	# Module Banks on this Assembly	1 Bank	01h	1 Bank	01h
6	Data Width of this Assembly...	x64	40h	x64	40h
7	...Data Width Continuation	x64	00h	x64	00h
8	Voltage Interface Standard for this Assembly	LVTTL	01h	LVTTL	01h
9	SDRAM Cycle Time at Max. Supported CAS Latency (CL), CL = X	CL = 3, 8.0 ns	80h	CL = 3, 10 ns	A0h
10	SDRAM Access from Clock @ CL = X	CL = 3, 6.0 ns	60h	CL = 3, 7.0 ns	70h
11	DIMM Configuration Type (Non-parity, Parity, ECC)	ECC	02h	ECC	02h
12	Refresh Rate/Type	15.625 μ s/Self-Refresh	80h	15.625 μ s/Self-Refresh	80h
13	SDRAM Width, Primary DRAM	x16	10h	x16	10h
14	Error Checking SDRAM Data Width	N/A	00h	N/A	00h
15	Minimum Clock Delay, Back-to-Back Random Column Addresses	1 CLK	01h	1 CLK	01h
16	Burst Lengths Supported	1,2,4,8 Full page	8Fh	1,2,4,8 Full page	8Fh
17	# Banks on Each SDRAM Device	4 Banks	04h	4 Banks	04h
18	CAS # Latencies Supported	2,3	06h	2,3	06h
19	CS # Latency		01h		01h
20	WE # Latency		01h		01h
21	SDRAM Module Attributes		00h		00h
22	SDRAM Device Attributes: General		0Eh		0Eh
23	Minimum Clock Cycle Time at CL- X-1	CL = 2, 10 ns	A0h	CL = 2, 12 ns	C0h
24	Maximum Data Access Time from Clock @ CL X-1	CL = 2, 6.0 ns	60h	CL = 2, 8.0 ns	80h
25	Minimum Clock Cycle Time at CL X-2		00h		00h
26	Maximum Data Access Time from Clock @ CL X-2		00h		00h
27	Minimum Row Precharge Time	20 ns	14h	24 ns	18h
28	Minimum Row-Active-to-Row-Active Delay	20 ns	14h	20 ns	14h
29	Minimum RAS-to-CAS Delay	20 ns	14h	24 ns	18h
30	Minimum RAS Pulse Width	48 ns	30h	60 ns	3Ch
31	Module/Bank Density	32 MB	08h	32 MB	08h
32	Command & address signal input Setup Time	2 ns	20 h	2.5 ns	25 h
33	Command & address signal input Hold Time	1 ns	10 h	1 ns	10 h
34	Data Signal input Setup Time	2 ns	20 h	2.5 ns	25 h
35	Data Signal input Hold Time	1 ns	10 h	1 ns	10 h
36-61	Superset Information (May Be Used in Future)		FFh		FFh
62	SPD Revision	Rev. 1.2A	12h	Rev. 1.2A	12h
63	Checksum for Bytes 0-62	1ECAh	CAh	1F58h	58h

OPTION

64	Manufacturers JEDEC ID Code per JEP-106E				
65-71					
72	Manufacturing Location				
73-90	Manufacturer's Part Number				
91-92	Revision Code				
93-94	Date of Manufacture				
95-98	Assembly Serial Number				
99-125	Manufacturer-Specific Data				
126	Reserved	Intel Specification	66h	Intel Specification	66h
127	Reserved	Intel Specification	87h	Intel Specification	87h
128-255					

BLOCK DIAGRAM



ABSOLUTE MAXIMUM RATINGS

SYMBOL	ITEM	RATING	UNIT	NOTES
V_{IN}	Input Voltage	- 0.3 to $V_{CC} + 0.3$	V	1
V_{OUT}	Output Voltage	- 0.3 to $V_{CC} + 0.3$	V	1
V_{DD}	Power Supply Voltage	- 0.3 to 4.6	V	1
T_{OPR}	Operating Temperature	0 to 70	°C	1
T_{STG}	Storage Temperature	- 55 to 125	°C	1
P_D	Power Dissipation	3.7	W	1
I_{OUT}	Short Circuit Output Current	50	mA	1

RECOMMENDED DC OPERATING CONDITIONS ($T_a = 0^\circ$ to 70°C)

SYMBOL	PARAMETER	MIN	TYP.	MAX	UNIT	NOTES
V_{DD}	Supply Voltage	3.0	3.3	3.6	V	2
V_{IH}	LVTTL Input High Voltage	2.0	-	$V_{DD} + 0.3$	V	2
V_{IL}	LVTTL Input Low Voltage	- 0.3	-	0.8	V	2

CAPACITANCE ($V_{CC} = 3.3\text{ V}$, $f = 1\text{ MHz}$, $T_a = 0^\circ$ to 70°C)

SYMBOL	PARAMETER	MIN	MAX	UNIT
C_{I1}	Input Capacitance (A0 to A11)	-	T.B.D	pF
C_{I2}	Input Capacitance ($\overline{\text{RAS}}$, $\overline{\text{CAS}}$, $\overline{\text{WE}}$, BA0,1)	-	T.B.D	pF
C_{I3}	Input Capacitance (CLK0)	-	T.B.D	pF
C_{I4}	Input Capacitance ($\overline{\text{CS0}}$,2)	-	T.B.D	pF
C_{I5}	Input Capacitance (DQMB0 to 7)	-	T.B.D	pF
C_{DQ}	I/O Capacitance (DQ0 to DQ63)	-	T.B.D	pF

DC CHARACTERISTICS ($V_{CC} = 3.3\text{ V} \pm 0.3\text{ V}$, $T_a = 0^\circ$ to 70°C)

SYMBOL	ITEM		-80		-10		UNIT	NOTES
			MIN	MAX	MIN	MAX		
I_{CC1}	OPERATING CURRENT Active-Precharge Command Cycling without Burst Operation ($t_{CK} = \text{min}$, $t_{RC} = \text{min}$)	1-Bank Operation	–	360	–	280	mA	3
I_{CC2}	STANDBY CURRENT ($t_{CK} = \text{min}$, $\overline{CS} = V_{IH}$, $V_{IH/L} = V_{IH}(\text{min}) / V_{IL}(\text{max})$ Bank: Inactive State)	CKE = V_{IH}	–	160	–	120	mA	3
I_{CC2P}		CKE = V_{IL} (Power-down Mode)	–	4	–	4		
I_{CC2S}	STANDBY CURRENT (CLK = V_{IL} , $\overline{CS} = V_{IH}$, $V_{IH/L} = V_{IH}(\text{min}) / V_{IL}(\text{max})$ Bank: Inactive State)	CKE = V_{IH}	–	40	–	40	mA	
I_{CC2PS}		CKE = V_{IL} (Power-down Mode)	–	4	–	4		
I_{CC3}	NO OPERATING CURRENT ($t_{CK} = \text{min}$, $\overline{CS} = V_{IH}(\text{min})$ Bank: Active State (2 Banks))	CKE = V_{IH}	–	240	–	180	mA	3
I_{CC3P}		CKE = V_{IL} (Power-down Mode)	–	32	–	32		
I_{CC4}	BURST OPERATING CURRENT ($t_{CK} = \text{min}$, $\overline{CS} = V_{IH}(\text{min})$, Read/Write Command Cycling)		–	480	–	360	mA	3, 4
I_{CC5}	AUTO-REFRESH CURRENT ($t_{CK} = \text{min}$, Auto-Refresh Command Cycling)		–	560	–	440	mA	3
I_{CC6}	SELF-REFRESH CURRENT (Self-Refresh Mode, CKE = 0.2 V)		–	4	–	4	mA	3
$I_{I(L)}$	INPUT LEAKAGE CURRENT ($0\text{ V} \leq V_{IN} \leq V_{DD}$, All Other Pins Not under Test = 0 V)		–5	5	–5	5	μA	
$I_{O(L)}$	OUTPUT LEAKAGE CURRENT (D_{OUT} Is Disabled, $0\text{ V} \leq V_{OUT} \leq V_{DD}$)		–5	5	–5	5	μA	
V_{OH}	OUTPUT LEVEL LVTTTL Output H Level Voltage ($I_{OUT} = -2\text{ mA}$)		2.4	–	2.4	–	V	
V_{OL}	OUTPUT LEVEL LVTTTL Output L Level Voltage ($I_{OUT} = 2\text{ mA}$)		–	0.4	–	0.4	V	

AC CHARACTERISTICS AND RECOMMENDED OPERATING CONDITIONS

(V_{CC} = 3.3 V ± 0.3 V, T_a = 0° to 70°C) (Notes 5, 6, 7)

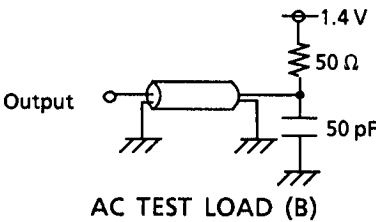
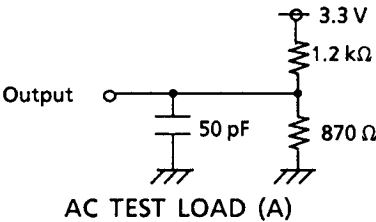
SYMBOL	PARAMETER		-80		-10		UNIT	NOTES
			MIN	MAX	MIN	MAX		
t _{RC}	Ref/Active-Ref/Active Command Period		68		84		ns	9
t _{RAS}	Active- Precharge Command Period		48	100000	60	100000		
t _{RCD}	Active-Read/Write Command Delay Time		20		24			
t _{CCD}	Read/Write(a) -Read/Write(b) Command Period		1		1		cycle	
t _{RP}	Precharge-Active Command Period		20		24		ns	10
t _{R RD}	Active(a)-Active(b) Command Period		20		20			
t _{WR}	Write Recovery Time	CL* = 2	10		12			
		CL* = 3	8		10			
t _{CK}	CLK Cycle Time	CL* = 2	10	1000	12	1000		
		CL* = 3	8	1000	10	1000		
t _{CH}	CLK High Level Width		3		3			
t _{CL}	CLK Low Level Width		3		3			
t _{AC}	Access Time from CLK	CL* = 2		6		8		
		CL* = 3		6		7		
t _{OH}	Output Data Hold Time		3		3			
t _{HZ}	Output Data High Impedance Time		3	8	3	10		8
t _{LZ}	Output Data Low Impedance Time		0		0			
t _{SB}	Power-down Mode Entry Time		0	8	0	10		
t _T	Transition Time of CLK (Rise and Fall)		0.5	10	0.5	10		
t _{DS}	Data-in Set-up Time		2		2.5			
t _{DH}	Data-in Hold Time		1		1			
t _{AS}	Address Set-up Time		2		2.5			
t _{AH}	Address Hold Time		1		1			
t _{CKS}	CKE Set-up Time		2		2.5			
t _{CKH}	CKE Hold Time		1		1			
t _{CMS}	Command Set-up Time		2		2.5			
t _{CMH}	Command Hold Time		1		1			
t _{REF}	Refresh Time			64		64	ms	
t _{RSC}	Mode Register Set Cycle Time		16		20		ns	9

* CL is $\overline{\text{CAS}}$ latency.

NOTES

- 1. Conditions outside the limits listed under Absolute Maximum Ratings may cause permanent damage to the device.
- 2. All voltages are referenced to Vss.
- 3. These parameters depend on the cycle rate and their values are measured at the minimum cycle rate value t_{CK} and t_{RC} . Input signals are changed once during t_{CK} .
- 4. These parameters depend on the output loading. The specified values are obtained with the output open.
- 5. The power-up sequence is described in Note 12.
- 6. AC TEST CONDITIONS

Reference Level of Output Signals	1.4 V / 1.4 V
Output Load	See the diagram for AC Test Load (B) below
Input Signal Levels	2.4 V / 0.4 V
Transition Time (Rise and Fall) of Input Signals	2 ns
Reference Level of Input Signals	1.4 V



- 7. Transition times are measured between the V_{IH} and V_{IL} levels. The transition (rise and fall) of input signals has a fixed slope.
- 8. t_{HZ} defines the time at which the outputs go open circuit and are not reference levels.

9. These parameters depend on the number of clock cycles and depend on the operating frequency of the clock as follows:

Number of clock cycles = Specified value of timing / Clock period
(Round up fractions to a whole number.)

10. t_{CH} is the pulse width of CLK measured from the positive edge to the negative edge and referenced to $V_{IH}(\min)$. t_{CL} is the pulse width of CLK measured from the negative edge to the positive edge and referenced to $V_{IL}(\max)$.

11. Power-up Sequence

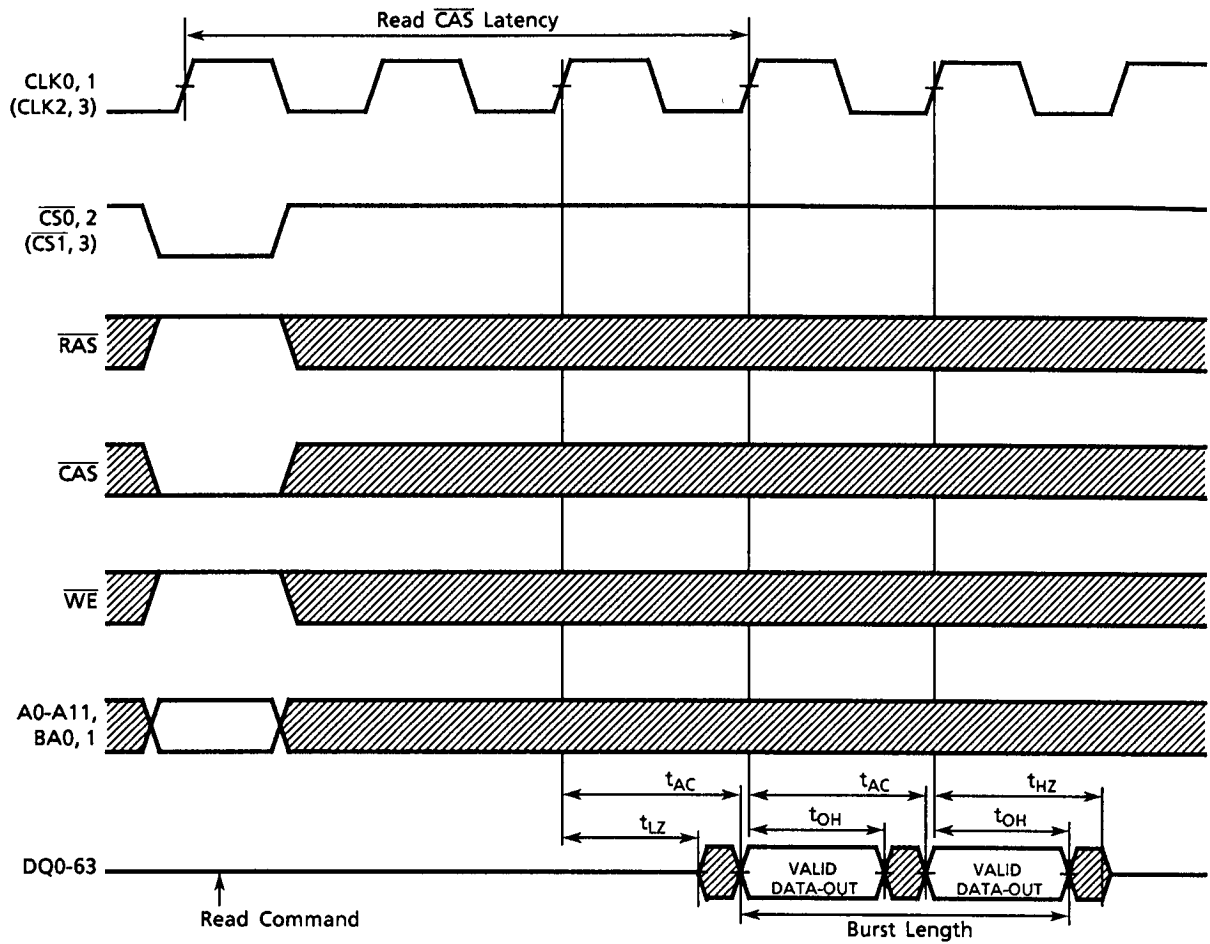
Power-up must be performed in the following sequence.

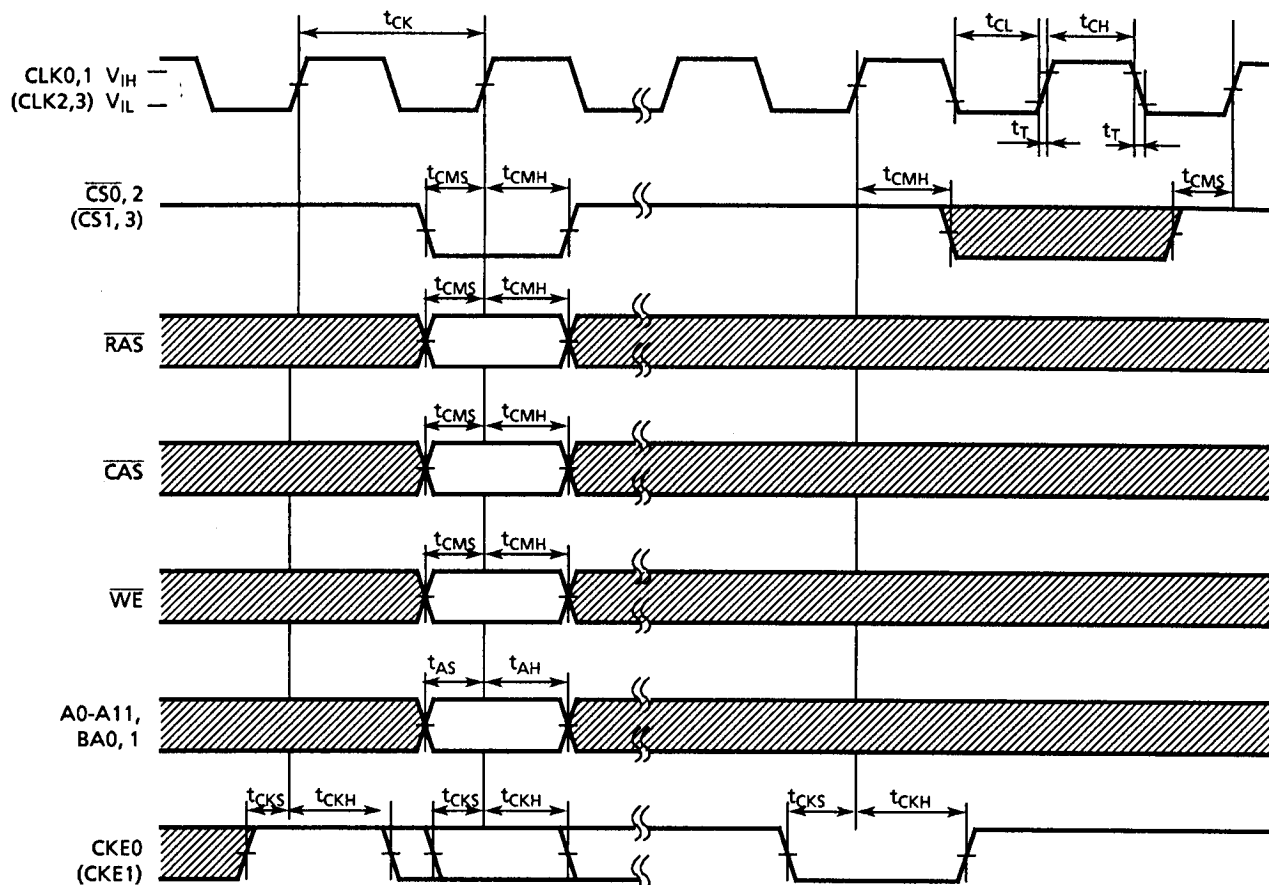
- 1) Power must be applied to V_{DD} with all input signals held in the NOP state. The CLK signal must be started at the same time as power is applied.
- 2) After power-up a pause of at least 200 μ seconds is required. Then, DQMB and CKE must be held High (at the V_{DD} level) to ensure that the DQ and CB outputs are high-impedance.
- 3) Both banks must be precharged.
- 4) The Mode Register Set command must be asserted to initialize the Mode register.
- 5) An Auto-Refresh operation must consist of at least eight Auto-Refresh cycles.

The order in which 4) and 5) are performed is interchangeable.

TIMING DIAGRAMS

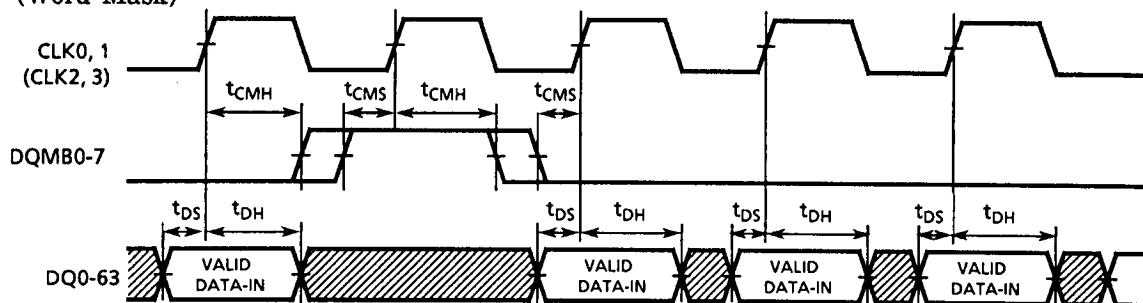
Read Timing



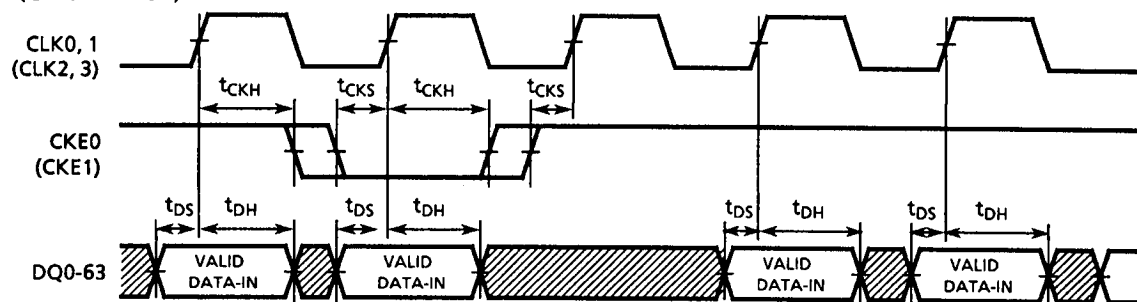
Command Input Timing

Control Timing for Input Data

(Word Mask)

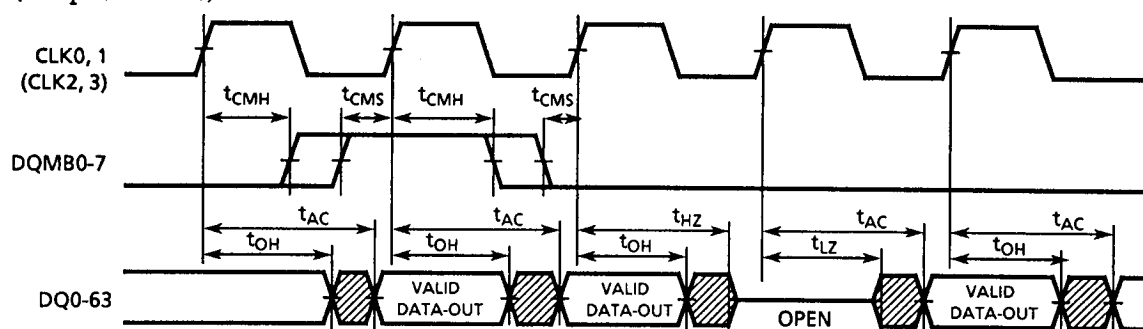


(Clock Mask)

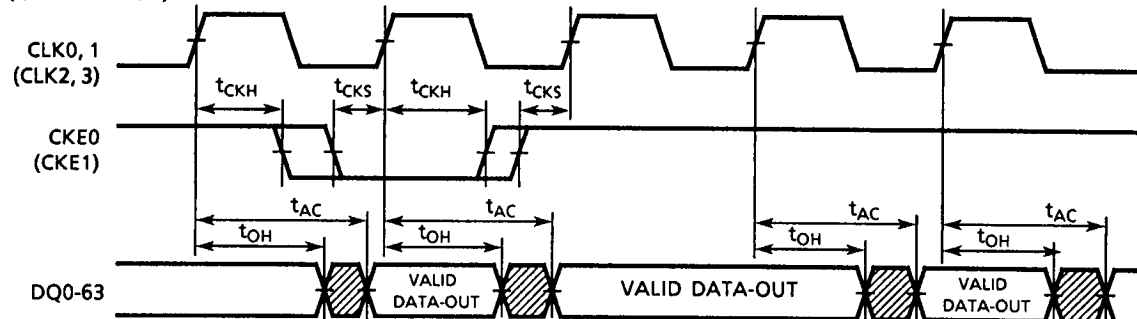


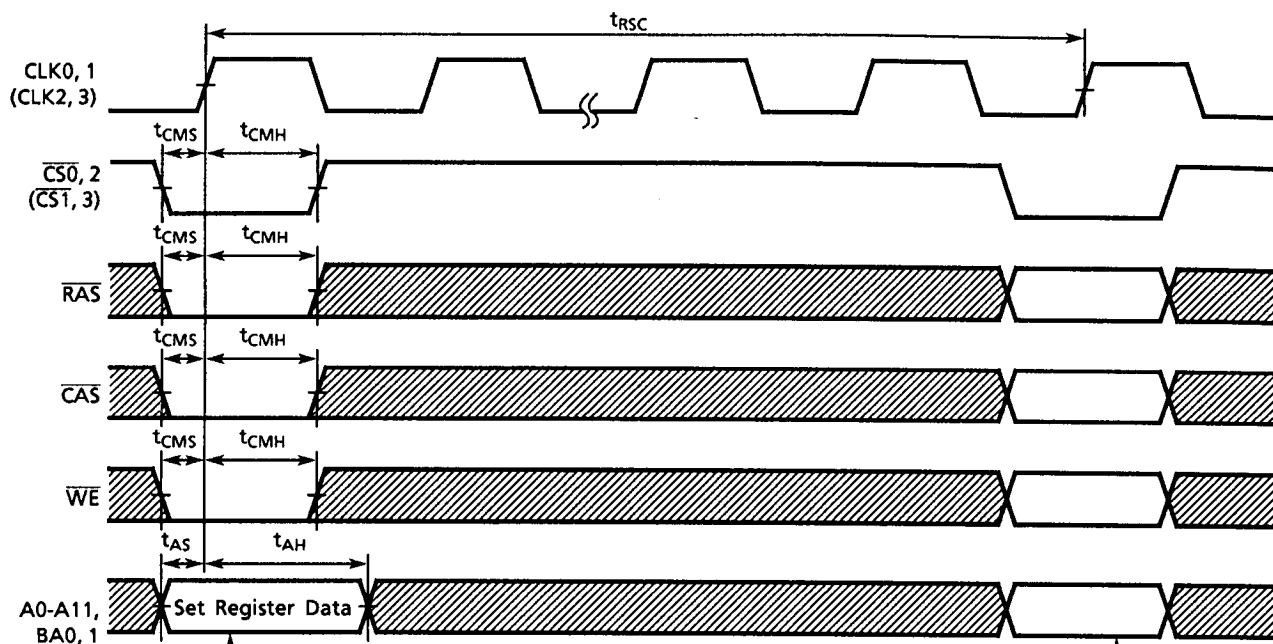
Control Timing for Output Data

(Output Enable)



(Clock Mask)



Mode Register Set Cycle

A0	Burst Length	
A1		
A2		
A3	Addressing Mode	
A4	CAS Latency	
A5		
A6		
A7	0	(Test Mode)
A8	0	Reserved
A9	Write Mode	
A10	0	Reserved
A11	0	
BA0	0	
BA1	0	

			Burst Length	
A2	A1	A0	Sequential	Interleave
0	0	0	1	1
0	0	1	2	2
0	1	0	4	4
0	1	1	8	8
1	0	0	Reserved	Reserved
1	0	1		
1	1	0	Full Page	Reserved
1	1	1		

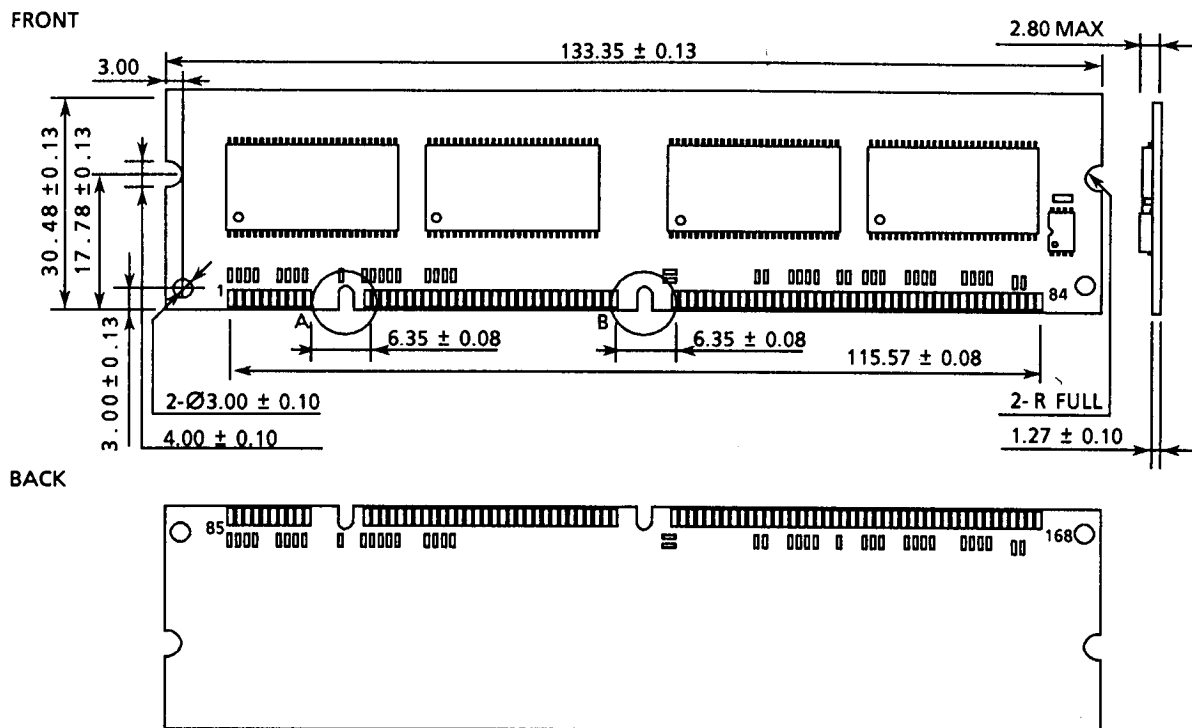
A3	Addressing Mode
0	Sequential
1	Interleave

A6	A5	A4	CAS Latency
0	0	0	Reserved
0	0	1	Reserved
0	1	0	2
0	1	1	3
1	0	0	4

A9	Single-Write Mode
0	Burst Read and Burst Write
1	Burst Read and Single Write

PACKAGE DIMENSIONS (THMY644071BEG)

Unit: mm



CONTACT DIMENSIONS

A: Unbuffered keying

B: 3.3-V keying

